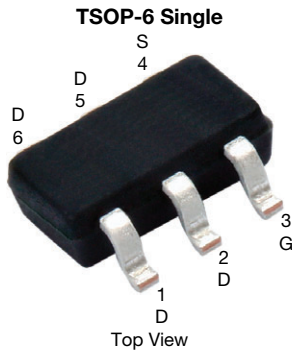


## Automotive P-Channel 12 V (D-S) 175 °C MOSFET

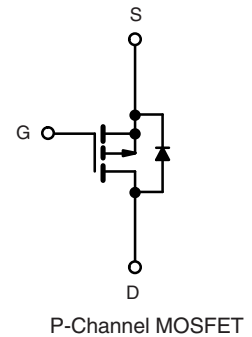


Marking Code: 8UY

### FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified °
- 100 % R<sub>G</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

 AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**


PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-12
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = -4.5 V	0.025
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = -2.5 V	0.032
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = -1.8 V	0.043
I <sub>D</sub> (A)	-8
Configuration	Single

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3461EV (for detailed order number please see <a href="http://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>	-12	V
Gate-source voltage	V <sub>GS</sub>	± 8	
Continuous drain current °	I <sub>D</sub>	T <sub>C</sub> = 25 °C	-8
		T <sub>C</sub> = 125 °C	-6.6
Continuous source current (diode conduction)	I <sub>S</sub>	-6.3	A
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	-30	
Single pulse avalanche current	I <sub>AS</sub>	-17	
Single pulse avalanche energy	E <sub>AS</sub>	14	mJ
Maximum power dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	5
		T <sub>C</sub> = 125 °C	1.67
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to ambient	R <sub>thJA</sub>	110	°C/W
Junction to case (drain)	R <sub>thJF</sub>	30	

### Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- Package limited



SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-12	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4	-0.6	-1	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = -12\text{ V}$	-	-	-1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = -12\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}, V_{DS} = -12\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-11	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -7.9\text{ A}$	-	0.021	0.025	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -6.6\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.033	
		$V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.037	
		$V_{GS} = -2.5\text{ V}, I_D = -7\text{ A}$	-	0.026	0.032	
		$V_{GS} = -1.8\text{ V}, I_D = -3\text{ A}$	-	0.036	0.043	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -7.9\text{ A}$	-	21	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = -6\text{ V}, f = 1\text{ MHz}$	-	1600	2000	$\text{pF}$
Output Capacitance	$C_{oss}$		-	620	770	
Reverse Transfer Capacitance	$C_{rss}$		-	490	620	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = -4.5\text{ V}, V_{DS} = -6\text{ V}, I_D = -7.9\text{ A}$	-	21	28	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$		-	2.5	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	7	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	2.8	5.7	8.6	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 1.6\text{ }\Omega, I_D \equiv -7.9\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$	-	12	17	ns
Rise Time <sup>c</sup>	$t_r$		-	52	68	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$		-	92	120	
Fall Time <sup>c</sup>	$t_f$		-	71	93	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>						
Pulsed Current <sup>a</sup>	$I_{SM}$		-	-	-20	A
Forward Voltage	$V_{SD}$	$I_F = -2\text{ A}, V_{GS} = 0\text{ V}$	-	-0.8	-1.2	V

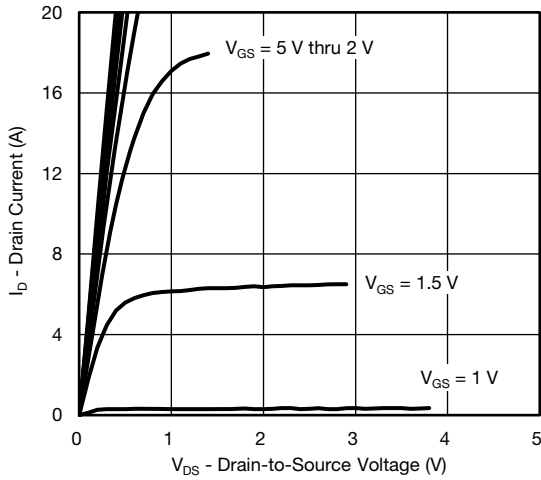
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

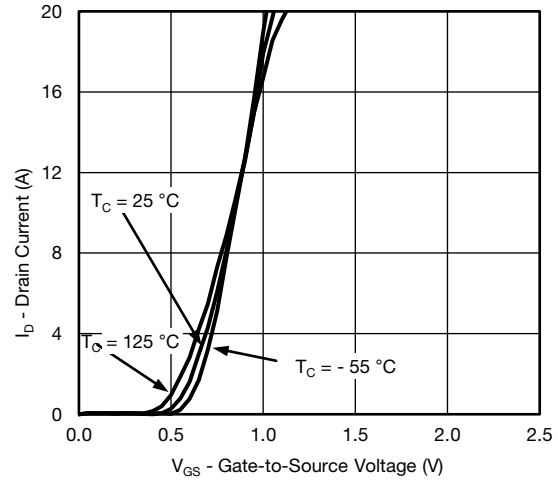
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



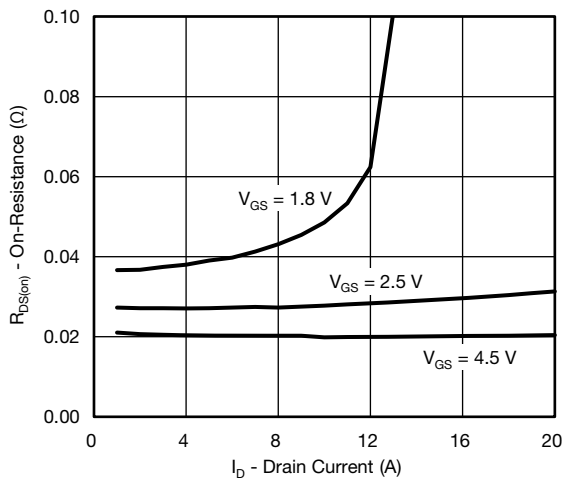
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



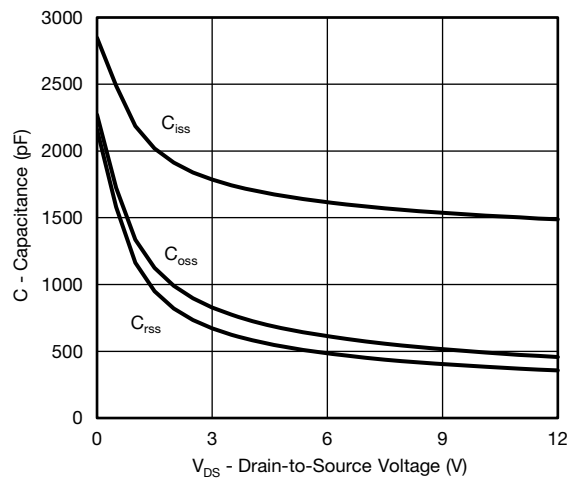
Output Characteristics



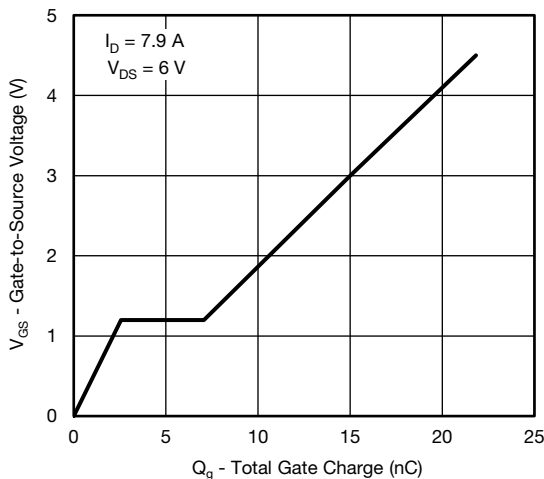
Transfer Characteristics



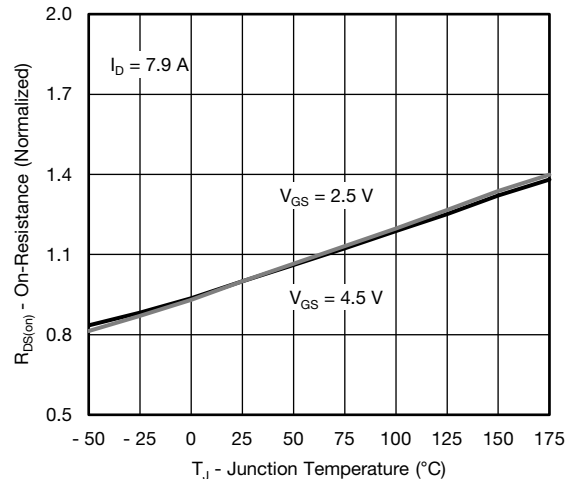
On-Resistance vs. Drain Current



Capacitance



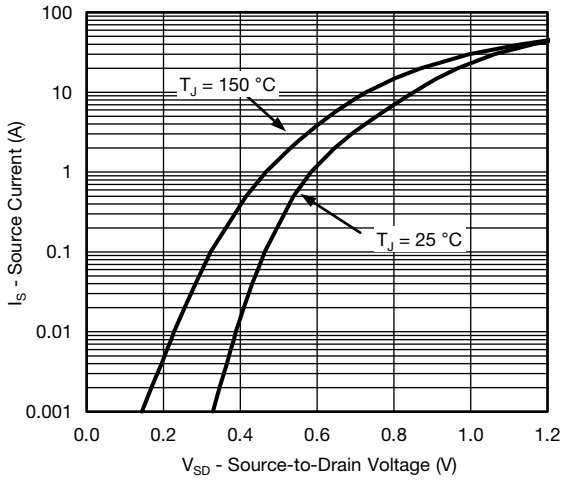
Gate Charge



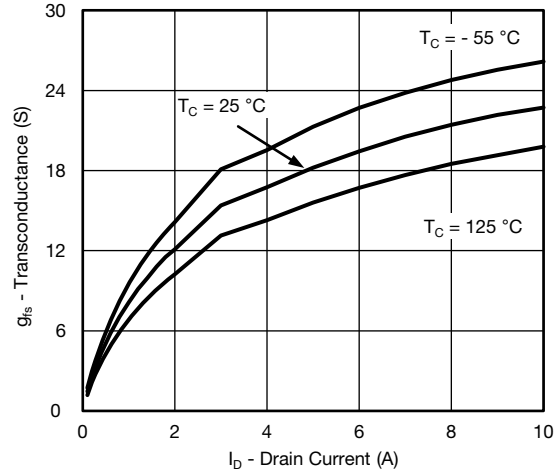
On-Resistance vs. Junction Temperature



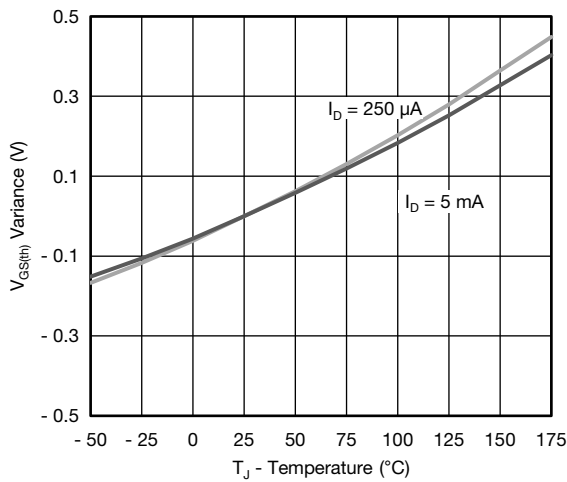
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



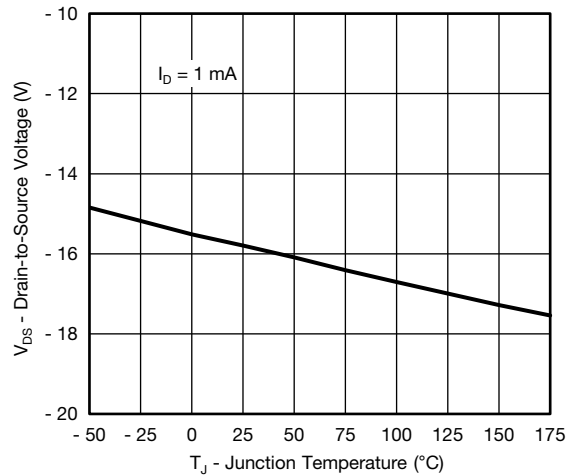
Source-Drain Diode Forward Voltage



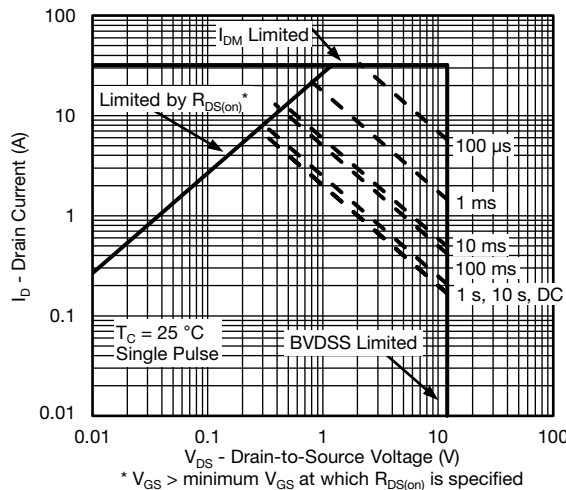
Transconductance



Threshold Voltage



Drain-to- Source Voltage vs. Junction Temperature



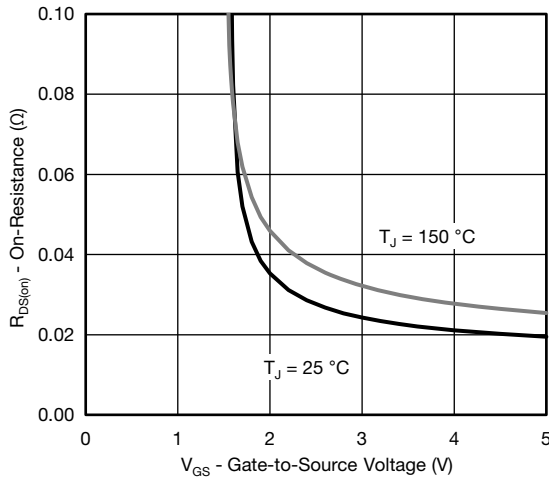
\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified



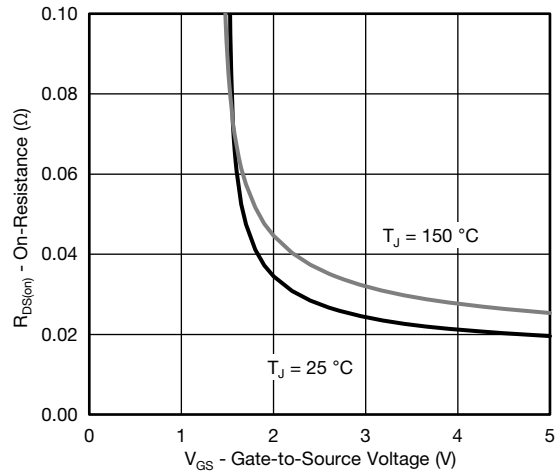
**Safe Operating Area**



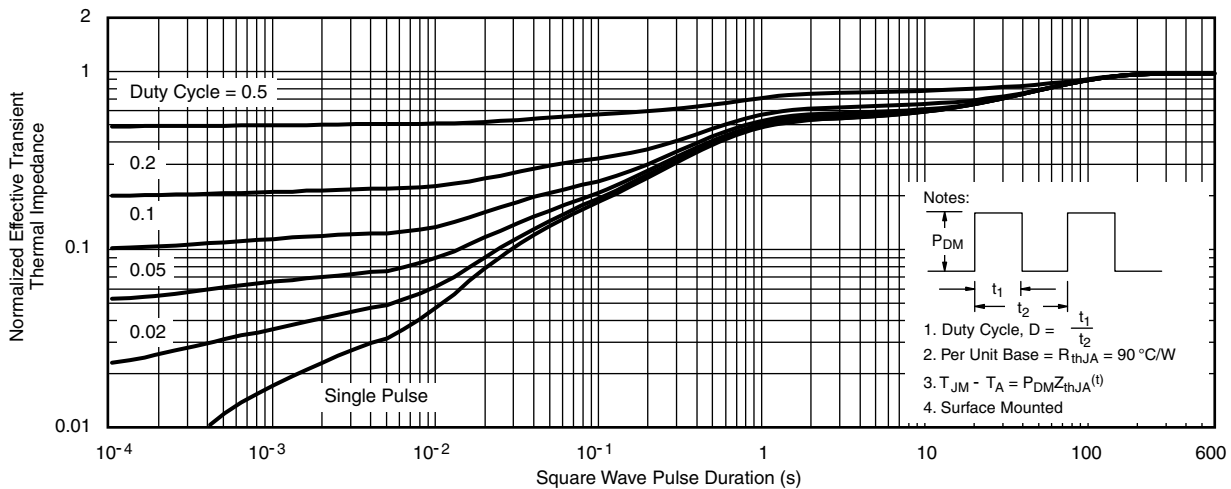
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Gate-to-Source Voltage (7.9 A)



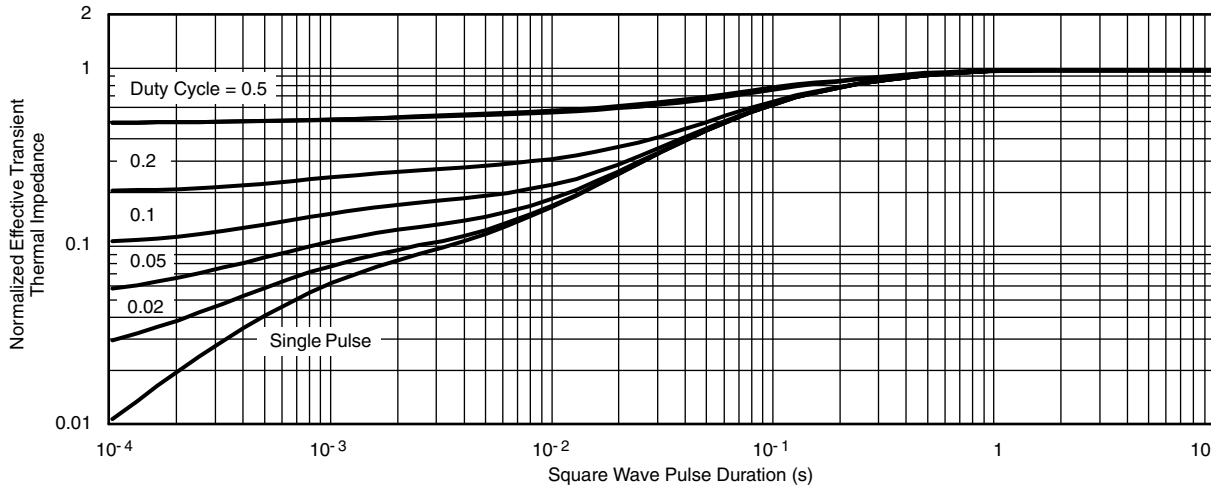
On-Resistance vs. Gate-to-Source Voltage (6.6 A)



Normalized Thermal Transient Impedance, Junction-to-Ambient



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Foot**

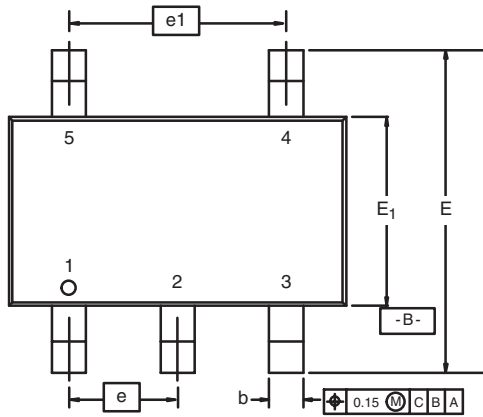
**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
    - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

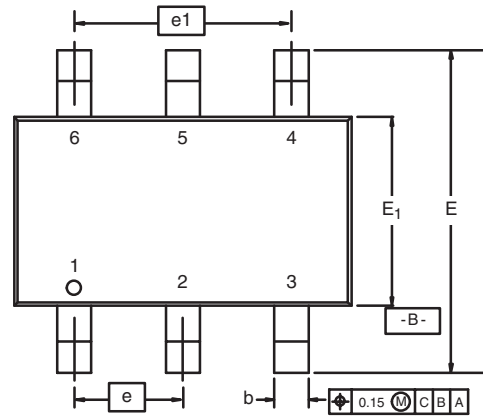
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## TSOP: 5/6-LEAD

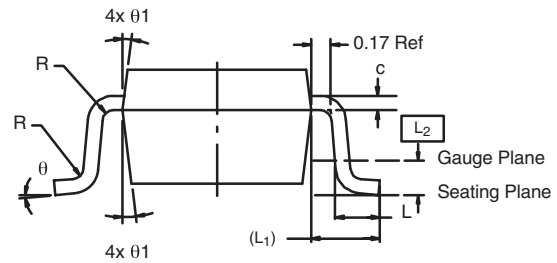
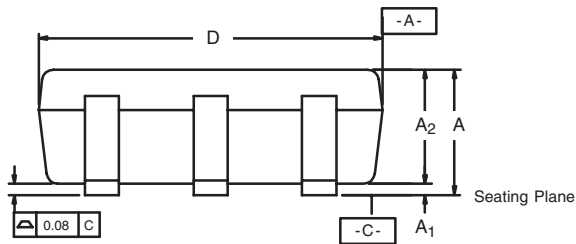
JEDEC Part Number: MO-193C



**5-LEAD TSOP**



**6-LEAD TSOP**

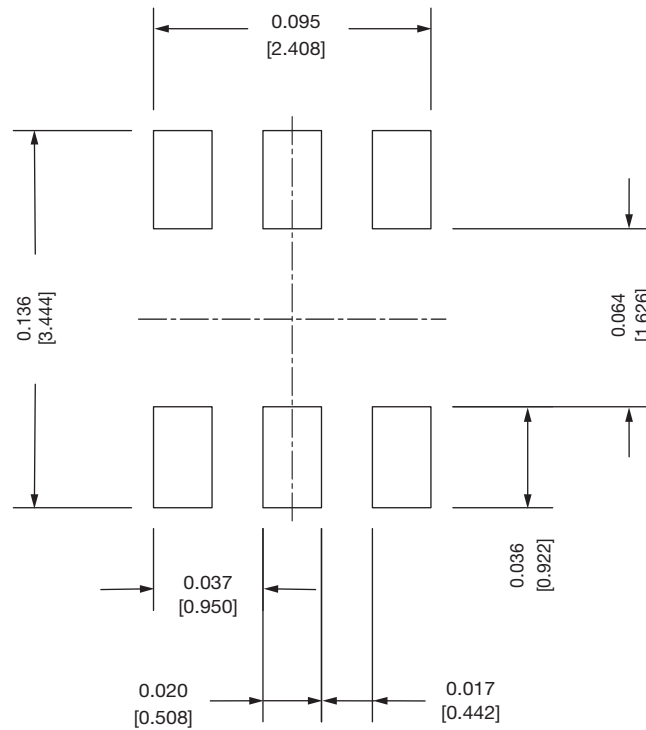
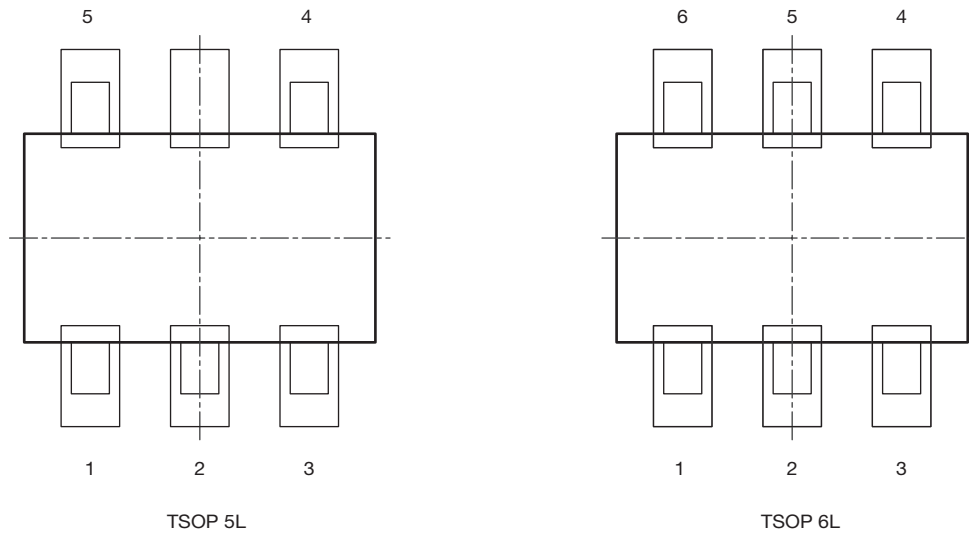


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
<b>A</b>	0.91	-	1.10	0.036	-	0.043
<b>A<sub>1</sub></b>	0.01	-	0.10	0.0004	-	0.004
<b>A<sub>2</sub></b>	0.90	-	1.00	0.035	0.038	0.039
<b>b</b>	0.30	0.32	0.45	0.012	0.013	0.018
<b>c</b>	0.10	0.15	0.20	0.004	0.006	0.008
<b>D</b>	2.95	3.05	3.10	0.116	0.120	0.122
<b>E</b>	2.70	2.85	2.98	0.106	0.112	0.117
<b>E<sub>1</sub></b>	1.55	1.65	1.70	0.061	0.065	0.067
<b>e</b>	0.95 BSC			0.0374 BSC		
<b>e<sub>1</sub></b>	1.80	1.90	2.00	0.071	0.075	0.079
<b>L</b>	0.32	-	0.50	0.012	-	0.020
<b>L<sub>1</sub></b>	0.60 Ref			0.024 Ref		
<b>L<sub>2</sub></b>	0.25 BSC			0.010 BSC		
<b>R</b>	0.10	-	-	0.004	-	-
<b>θ</b>	0°	4°	8°	0°	4°	8°
<b>θ<sub>1</sub></b>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						





# Recommended Land Pattern For TSOP-5L / TSOP-6L



**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
 DWG: 3010



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